

INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/530063
	Filing Date	
	First Named Inventor	Philippe Meunier-Beillard
	Art Unit	2823
	Examiner Name	Michelle Estrada
	Attorney Docket Number	BE02 0027 US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number No.-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number (ctry ³ -no.-kind ² , if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of cited document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		WO 01/14619	03-01-2001	JUERGENSEN HOLGER ET AL		

NON-PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in capital letters), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁴
		KLUMPP A ET AL: "AMPORPHOUS SILICON CARBIDE AND ITS APPLICATION IN SILICON MICROMACHINING" SENSORS AND ACTUATORS A, ELSEVIER SEQUOISA S.A., LAUSANNE, CH, VOL. A41, NO. 1/3, 1 APRIL 1994	
		VON MUNCH W ET AL: "NEW SUSCEPTOR ARRANGEMENT FOR THE EPITAXIAL GROWTH OF BETA-SIC ON SILICON" JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING CO., AMSTERDAM, NL, VOL 158, NO. 4, 1 FEBRUARY 1996	
		NORDELL N ET AL: "GROWTH OF SIC USING HEXAMETHYLDISILANE IN A HYDROGEN-POOR AMBIENT" APPLIED PHYSICS LETTERS, AMERICAN INST. OF PHYSICS. NEW YORK, NY, VOL. 64, NO. 13, 28 MARCH 1994 PAGES 1647-1649	
		KOBAYASHI S ET AL: "INITIAL GROWTH CHARACTERISTICS OF GERMANIUM ON SILICON IN LPCVD USING GERMANE GAS" JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING CO., AMSTERDAM, NL, VOL. 174, NO 1-4, 1 APRIL 1997	

Examiner Signature	Michelle Estrada	Date Considered	3/16/06
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.